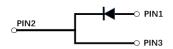




Silicon Carbide Schottky Diode

V_{RRM}	1200V
I _F (135°C)	12A
Q _C	37nC





Features

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
- Unipolar devices and zero reverse recovery current
- Zero forward recovery current
- Essentially no switching losses
- Reduction of heat sink requirements
- High-frequency operation
- Reduction of EMI

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

Package: TO-252
 Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant, halogen-free

• Terminals: Tin plated leads

• Polarity: As marked

■Maximum Ratings (T_C=25°C Unless otherwise specified)

PARAMTETER	SYMBOL	UNIT	VALUE
Device marking code			D112008DQG3
Reverse voltage (repetitive peak) @ T _j =25°C	V_{RRM}	٧	1200
Reverse voltage (Surge Peak) @ T _j =25°C	V_{RSM}	V	1200
Reverse voltage (DC) @ T _j =25°C	V_{DC}	V	1200
Continuous forward current @ T _c =25°C			25
Continuous forward current @ T _C =135°C	I _F	Α	12
Continuous forward current @ T _C =154°C			8
Non-repetitive peak forward surge current @ T _C =25°C, tp=10ms, Half Sine Wave	I _{FSM}	А	95
Power Dissipation@ T _C =25°C	D	W	126
Power Dissipation@ T _C =110°C	P _{TOT}		54
i²t Value@ T _C =25°C ,tp=10ms	∫ i²dt	A ² S	45
Operating junction and Storage temperature range	T_{j} , T_{stg}	°C	-55 to +175





■Electrical Characteristics

PARAMTETER	SYMBOL	UNIT	TEST CONDITIONS	Тур.	Max.	
E	.,,	F V	I _F =8A, T _j =25°C	1.46	1.55	
Forward voltage drop	V _F		I _F =8A, T _j =175°C	2.2	-	
Reverse leakage current I _R			V _R =1200V, T _j =25°C	1	10	
	μΑ	V _R =1200V, T _j =175°C	5	-		
Total capacitive charge	Q _C	nC	$\begin{array}{c} V_R = 800V, \ T_j = 25^{\circ}C \ , \\ Q_C = \int_0^{VR} C(V) dV \end{array}$	37	-	
				V _R =0V, f=1MHZ	500	-
Total capacitance C pF	pF	V _R =400V, f=1MHZ	35	-		
		V _R =800V, f=1MHZ	27	-		
Capacitance Stored Energy	Ec	μJ	V _R =800V	9.5	-	

■Thermal Characteristics (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE
Thermal resistance	R _{eJ-C}	°C W	1.19

■Typical Characteristics

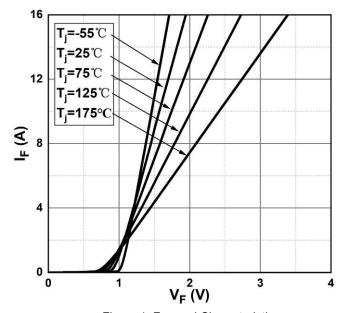


Figure 1. Forward Characteristics

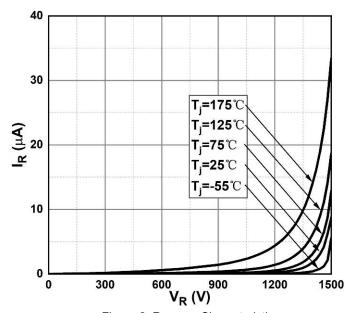
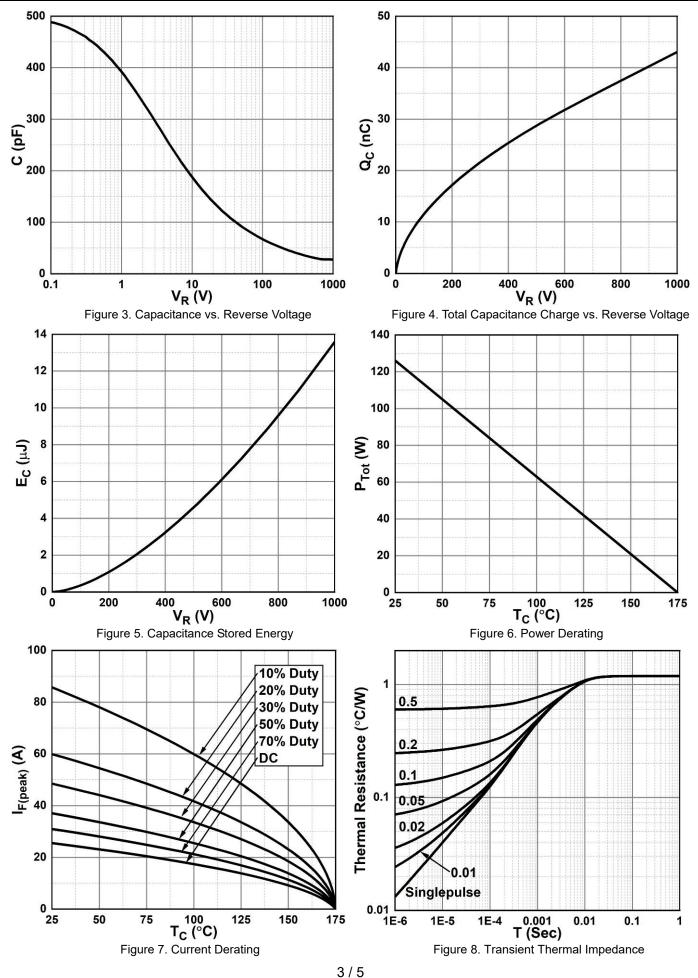


Figure 2. Reverse Characteristics



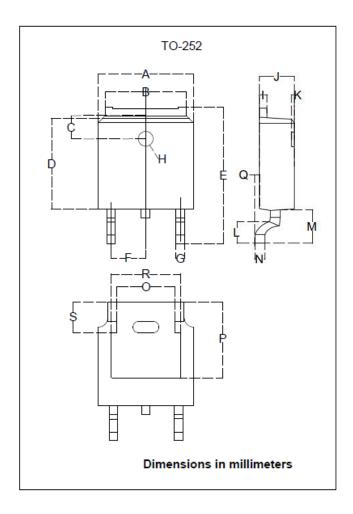






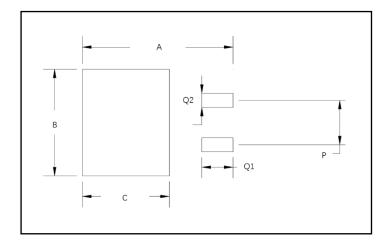


■Outline Dimensions



TO-252			
Dim	Min	Max	
Α	6.500	6.700	
В	5.100	5.460	
С	1.400	1.800	
D	6.000	6.200	
Е	10.000	10.400	
F	2.166	2.366	
G	0.660	0.860	
Н	Ф1.050	Ф1.350	
I	0.460	0.580	
J	2.200	2.400	
K	0	0.300	
L	0.890	2.290	
М	2.730	3.080	
N	0.430	0.580	
0	4.20	4.95	
Р	5.15	5.45	
Q	0	0.2	
R	4.50	5.10	
S	1.60	2.40	

■Suggested Pad Layout



Dim	Millimeters
Α	11.4
В	6.74
С	6.23
Р	4.56
Q1	2.28
Q2	1.52



YJD112008DQG3



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